# Si nanopyramid textures enabling solution-processed perovskite for tandem solar cell application

#### **Motivation**

### **Double-sided textured tandem solar cells**



Silicon cell

Transparent conducting oxide lectrode

#### ✓ EPFL: 31.25%<sup>[1]</sup> ✓ Longi: 33.9%<sup>[2]</sup>

Micron-sized Si pyramids + evaporated perovskite

#### ✓ HZB: 29.8%<sup>[3]</sup>

Si nanopyramids by nanoimprint lithography + spin-coated perovskite

**Merits** 

Reduced light reflection at the perovskite/Si interface.

#### **Problems**

• Technically complex/expensive methods for the conformal growth of perovskite on micrometer-sized Si pyramid texture.

 Complex fabrication process of nano-sized Si pyramid texture by lithography.







Aim of this work

Development of Si nanopyramids compatible with solution processed perovskite

**Our technology** 

One step wet etching process to fabricate Si nanopyramids

We investigated the effect of varying Si texture size in nanoscale on the performance of perovskite/Si tandem cells.

Temperature	70°C	70°C	70°C	70°C	80°C
Time	15min	5min	15min	15min	15min

**TK81**: moderate etching speed / H<sub>2</sub> bubbles detachment **AgNO**<sub>3</sub>: etching mask / H<sub>2</sub> bubbles detachment





- The size of the Si pyramid texture gradually decreases as the concentration of surfactant TK81 and AgNO<sub>3</sub> increases.
- The size distribution also narrows with the reduction of texture size.



- Reflectivity increases with decreasing Si pyramid size.
- Nevertheless, nanometer-sized Si pyramids show effective anti-reflective properties in device structure (w. ITO), resulting in comparable cell performance with the reference cell.<sup>[4,5]</sup>

## **Results (II)**

ITO

#### Current density-voltage (J-V) curves A(420nm) Spiro-MeOTAD B(530nm \*Device area : 1 cm<sup>2</sup> Perovskite - E(1050nm n) nc-Si:H (p) a-Si:H i) a-Si:H perovskite (n) c-Si

0.0 0.2 0.4 0.6 0.8 1.0 1.2 1.4 1.6 1.8 2.0

Voltage (V)

## **Tandem cell performance**<sup>[5]</sup>

**Cross-sectional SEM images** 

## **External quantum efficiency (EQE)**



Low V<sub>oc</sub> caused by electrical shunting due to the non-uniform perovskite layers on large Si texture.

) a-Si:H า) a-Si:H

- A substantial increase in  $V_{OC}$  from 0.89 to 1.75 V with decreasing the texture size from ~1000 to ~500 nm.
- $\blacksquare$  B(530nm) shows both high V<sub>OC</sub> and J<sub>SC</sub> (0.8 mA cm<sup>-2</sup> higher compared to the reference cells).
- Degraded passivation quality of a-Si:H layers when deposited on small-sized Si texture (A(420nm)), strongly depending on the PECVD conditioning.
- The light in-coupling effect of the Si nanopyramid texture leads to a gain in the  $J_{bottom}$  by ~1 mA cm<sup>-2</sup>.
- $\blacksquare$  J<sub>SC</sub> is further improved after applying the AR(MgF<sub>2</sub>) layer, leading to a 22.1% efficient tandem solar cell ( $J_{SC}$ =18.8 mA cm<sup>-2</sup>,  $V_{OC}$ =1.693 V, FF=0.692, area=1.0  $cm^2$ ).
- J<sub>SC</sub> is still limited by the large reflection loss caused by refractive index mismatching at the interface between the ITO ( $n \sim 2.0$ ) and the thick spiro-MeOTAD  $(n \sim 1.6)$  layers.

## Conclusions

Double-sided Si nanopyramid textures with an average size of 400-900 nm and improved size distribution were fabricated using an original Ag-assisted alkaline etching method and applied in the bottom cell of perovskite/Si tandem cells.

## References

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- Excessive size of pyramid causes the severe shunting and thickness inhomogeneity in the perovskite absorber layer, resulting in the degradation in the performance of tandem cells.
- The optimum Si texture size is found to be 400-500 nm with perovskite layer thickness around 500 nm, by which the perovskite top cell can be processed entirely by the conventional spin-coating method.
- > The both-sided nanopyramid Si texture shows great potential for the costeffective tandem cell manufacturing using the solution-based top cell process with enhanced J<sub>bottom</sub> and efficiency compared with the commonly used single-sided textured Si.
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